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December 17, 2003

Chemistry of Materials

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UCRL-JRNL-201517

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Abstract

We report the first measurements of anisotropy in magnetic susceptibility, magnetization, and electrical resistivity using single crystals of GdTSb₃ (T=Cr, V). GdTSb₃ is a quasi-two dimensional system with orthorhombic crystal structure (space group Pbcm). Unlike the other light rare earth chromium antimonides (R = Ce-Nd, Sm), in which two magnetic transitions are observed, GdCrSb₃ undergoes a single ferrimagnetic transition at T_C =86 K, which is evident in both the magnetic susceptibility and electrical resistivity. Within the b-c plane, GdCrSb₃ is found to have metallic behavior from 5 K to 300 K, but it is found to have insulating behavior ($d\rho_a/dT < 0$) along the stacking axis. GdVSb₃ is found to have a Néel transition at 5 K due to the localized Gd ions, but no ferromagnetic transition.

Key words: magnetism, antimonides, resistivity, RCrSb₃

PACS: 75.30.Gw, 72.80.Ga, 72.15.-v, 75.30.Cr

1 Introduction

The family of compounds, $RCrSb_3$ (R = La-Nd, Sm, Gd-Dy), have had many investigations in the literature due to their unique magnetic and electrical transport properties [1–12]. The parent member in the series, LaCrSb₃, has been studied in depth [3-5] because it has only one magnetic ion, Cr, yet it has a very complex magnetic phase diagram. It has been found to have a Curie temperature at $T_C=132$ K, followed by a spin reorientation phase for T <98 K and H <250 G due to the unconventional magnetism involving the coexistence of local and itinerant Cr moments.[4,5] While the itinerant ferromagnetic (FM) phase continues to exist for $RCrSb_3$ (R = Ce-Nd, Sm), a second low temperature magnetic phase occurs due to the ordering of the rare-earth ions. [6–10] SmCrSb₃ was found to be unique in the series due to the presence of a first order AFM transition at 30 K due to the ordering of the Sm ions. [10] Polycrystalline samples of R=Gd, Tb, and Dy have been investigated, [7,12] which show only one AFM transition, but the value of the transition temperature is still debated. Single crystal electrical resistivity measurements have also been collected along the c-axis, |12| but to our knowledge, this is the first report of the magnetization and electrical resistivity along all three principle axis of GdCrSb₃ using high quality single crystals.

2 Experimental Technique

Single crystals of $GdTSb_3$ were prepared from ingots of the elements [Gd from Ames Laboratory; Cr (99.996%), V (99.5%), and Sb (99.99%) from Alfa Æsar], and the growth procedure has been previously described[4]. $GdTSb_3$

crystallizes in an orthorhombic structure (space group Pbcm),[1,2] and consists of two distinct planar layers of Cr and Sb perpendicular to the a-axis which are separated by Gd ions (see Fig. 1a). The first of these layers consists of chains of Cr atoms extending along the c direction, with Sb atoms forming face sharing (edge sharing) octahedra along the c-axis (b-axis). The Gd ions lie in a checker board type pattern which alternates above and below the Sb plane. This quasi-2D crystal structure suggests that anisotropy may play a crucial role in understanding its properties. The lattice parameters were determined using a commercial Scintag x-ray diffractometer using a Si standard, and a least squares fit to a minimum of 20 peaks. The lattice constants for GdCrSb₃ were determined to be a = 12.75(6) Å, b = 6.15(2) Å, and c = 6.01(4) Å, and for GdVSb₃, a = 12.82(2) Å, b = 6.22(3) Å, and c = 5.96(2) Å.

Magnetization and magnetic susceptibility measurements were taken with a commercial superconducting quantum interference device (SQUID) magnetometer (Quantum Design MPMSR2) in the temperature range 2-350 K and -55 kG $\leq H \leq$ 55 kG. High field magnetization measurements were collected using a vibrating sample magnetometer in a field range of $0 \leq H \leq$ 31 T at the National High Magnetic Field Laboratory. Electrical resistivity measurements were performed using a standard four probe technique in the temperature range 5-295 K. All measurements were collected on as grown samples.

3 Magnetization

One expects $GdCrSb_3$ to have somewhat different properties than the light rare-earth antimonides in the series because Gd^{3+} has a half full f-electron shell, and therefore has zero orbital angular momentum and a large effective moment ($\mu_{eff} = 7.94 \ \mu_B$ according to Hund's Rules). Fig. 1 shows the field-cooled magnetization as a function of temperature with an applied field of 1 kG. Unlike the previous members in the series, there is no evidence of a FM phase for GdCrSb₃, but it does undergo a magnetic transition at T_C =86 K. This is most easily observed as a peak along the c-axis, and is consistent with this being the easy axis of a ferrimagnetic phase, and is the only apparent magnetic phase transition. Fig. 1 also shows an upturn in the susceptibility at low temperatures along both the a and b-axis, which may be due to the Cr vacancies which are known to exist in these compounds.[5] These vacancies may play a role in the discrepancies in the reported transition temperatures. For example, Deakin $et \ al$ report a value of 92 K for the magnetic transition,[12] and Leonard $et \ al$ report a value of 26 K.[7]

The high temperature inverse susceptibility (T > 200 K) was fit to a modified Curie–Weiss law, $1/(\chi - \chi_0) = (T - \theta)/C$, where χ_0 is the temperature independent susceptibility, θ is the Curie temperature, and C is the Curie constant. The data is shown in Fig. 1b, with the values from the fit given in Table 1. The expected value of χ_0 can be approximated to be approximately -1×10^{-4} emu/mol[13], which is an order of magnitude larger than what is found for this system. This, as well as the metallic electrical resistivity, is consistent with itinerant behavior for the RCrSb₃ family. Table 1 also lists the effective moment of GdCrSb₃ for each axis. A polycrystalline average gives $\mu_{eff} = 9.21 \,\mu_B/\text{f.u.}$, which is larger than the value predicted by Hund's Rules, but close to the value of 8.16 $\mu_B/\text{f.u.}$, obtained by Deakin et~al.[12] They suggest that this large value is an indication of the strong interactions of the 3d and 4f moments above the ordering temperature. The downward curvature seen in the inverse susceptibility near T_C (Fig. 1b) is the expected behavior

for a ferrimagnetic system.

The magnetization as a function of applied magnetic field (Fig. 2) also suggests that below T_C =86 K, GdCrSb₃ is ferrimagnetic. At 5 K, one finds that M_a and M_b linearly increase with increasing field, while M_c undergoes a spin-flop transition at 26 kG, which implies that the easy axis is parallel to the Cr chains (the c-axis). The inset to Fig. 2 shows the magnetization along the a-axis up to 31 T at 10 K and 75 K. The a-axis magnetization begins to saturate just below 15 T to a value of 5.6 μ_B /f.u., which is smaller than the predicted saturation value of Gd³⁺ ($\sigma = gJ = 7 \mu_B$).

4 Electrical Resistivity

The distinctive behavior of the magnetization leads one to expect unique electrical resistivity as well, and Fig. 3 shows that this is found to be true. The initial high temperature behavior of the electrical resistivity is similar to both LaCrSb₃ and SmCrSb₃,[4,10] with positive temperature dependence for the in-plane (b-c plane) resistivity, and non-metallic ($d\rho/dT < 0$) temperature dependence for the out of plane (a-axis) resistivity. Below T_C , the in-plane resistivity continues to have a positive slope. While the residual resistivity ratio for both axis ($RRR_b = 0.45$, $RRR_c = 0.70$) is small, the values are larger than what has been observed in other members of the series. For example it is approximately three times larger than LaCrSb₃ ($RRR_b = 0.16$, $RRR_c = 0.23$),[4] and twice as large as SmCrSb₃ ($RRR_b = 0.19$, $RRR_c = 0.34$).[10] This small value is likely due to the large number of Cr vacancies, such as has been observed for LaCrSb₃.[5] For R=La-Nd, and Sm, the resistivity along the a-axis (the stacking axis) was found to have a change in the sign of the slope below

 T_C , but for GdCrSb₃, a kink is observed, below which the resistivity continues to rise with an increased slope. Fig. 3a shows that a Fisher-Langer-type anomaly is present along the b-axis (as well as the c-axis, data not shown), only the peak has become broadened compared with LaCrSb₃ and SmCrSb₃. Below T_C , Fig. 3b shows that the in-plane resistivity decreases as $T^{3/2}$, which is the same behavior found for both R=La[4] and Sm.[10] This temperature dependence for the electrical resistivity is common for a FM systems in which the scattering length is reduced from an ideal system,[14] which suggests that the in-plane scattering mechanism for GdCrSb₃ is similar to that found for R=La and Sm.

5 GdVSb₃

LaVSb₃ was found to be a non-magnetic counterpart to LaCrSb₃. Therefore, in order to understand the properties of GdCrSb₃ in the absence of itinerant magnetism, isostructural GdVSb₃ was investigated. The in-plane anisotropy in the magnetization for GdVSb₃ was found to be zero. Therefore Fig. 4a shows only the data along the c-axis, with a modified Curie–Weiss fit between 45 K and 330 K, and the resulting parameters given in Table 1. The low temperature susceptibility is shown in the inset to Fig. 4a in which a peak is found at T_N =5 K. This is very similar behavior to that seen in SmVSb₃.[10] The values obtained are close to the expected value for Gd³⁺ of $\mu_{eff} = 7.94 \, \mu_B$.

The electrical resistivity normalized at room temperature is shown in Fig. 4b. Both axes have similar behavior to what was found for SmVSb₃,[10] only the AFM ordering temperature for GdVSb₃ is large enough that an initial increase in the resistivity just above 5 K can be seen. Due to the small thickness, it

was not possible to measure the electrical resistivity along the a-axis.

6 Discussion

GdVSb₃ is isostructural to GdCrSb₃, but, like LaVSb₃, in which the magnetic susceptibility is small and temperature independent due to the absence of itinerant magnetism, [4] the magnetic susceptibility of GdVSb₃ is due only to the localized 4f-electrons of Gd³⁺. It is magnetically isotropic, unlike GdCrSb₃, and it has a Néel temperature near 5 K due to ordering of the 4f-moments. This points to the importance of the interactions between the itinerant 3d-electrons and the localized 4f-electrons in determining the properties of the RCrSb₃ family of materials.

RCrSb₃ (R = Ce-Nd, and Sm) are all found to undergo two magnetic transitions due to the itinerant FM phase of the 3d-electrons at high temperatures, followed by a low temperature ordering of the localized rare-earth ions.[6–10] For R = Sm and Gd, the interactions between the itinerant 3d and localized 4f-electrons are strong enough to bring about unique properties in these two materials. SmCrSb₃ was found to undergo a first order Néel transition at 30 K, and isothermal magnetization hysteresis loops observed at low fields below T_N suggest that the itinerant 3d-electrons continue to exhibit FM interactions, but the localized 4f-moments nearly cancel out the macroscopic magnetization of the sample.[10] Although our magnetization results can not probe the microscopic behavior of the 3d and 4f-moments, it would be consistent with the SmCrSb₃ results for the compound to be described by two independent, yet heavily interacting subsystems: one composed of itinerant 3d-electrons, and a second of anti-aligned localized 4f-moments.

It is believed that similar behavior is found for GdCrSb₃, but for this material, both magnetic lattices order at the same temperature and appear to be antiparallel, resulting in a complex ferrimagnetic ordering. The downward curvature in $1/\chi$ just above T_C (Fig. 1b) is indicative of ferrimagnetism. Recent ac magnetic susceptibility measurements of GdCrSb₃[12] show a significant imaginary component to the magnetic susceptibility, which provides further support for a ferrimagnetic phase. The spin-flop transition at 26 kG and 5 K is also consistent with a ferrimagnetic phase, and indicates the easy axis is along the c-axis. At 30 K, Deakin et al. [12] observed a maximum in the magnetoresistance at 30 kG when the magnetic field was oriented along the c-axis, and no maximum with the magnetic field aligned perpendicular to the c-axis. The inplane $T^{3/2}$ resistivity behavior of GdCrSb₃ is also similar to both LaCrSb₃ and SmCrSb₃, suggesting that the scattering mechanisms are similar, which would again be consistent with itinerant ferromagnetism due to the 3d-electrons below T_C =86 K, but strong interactions with the 4f-moments resulting in an overall ferrimagnetic phase.

The transition temperatures for $R\text{CrSb}_3$ (R = La-Nd, Sm, and Gd) are plotted vs the de Gennes factor, $DG = (g-1)^2 J(J+1)$, in Fig. 5. This shows that the FM transition due to the itinerant 3d-electrons of the Cr ions, as well as the localized 4f-moments of the rare-earth ions scale with the de Gennes factor. In addition, both transition temperatures converge at the ferrimagnetic transition found for GdCrSb₃. The result provides further evidence of the behavior of the ferrimagnetic phase in which the Gd and Cr moments strongly interact, and become anti-aligned at the same temperature. The inset to Fig. 5 shows the paramagnetic Curie temperature, averaged over the three principle axis, for each member in the series. Although a general downward trend is observed, it

is not clear if there is a strong correlation between the de Gennes factor and the paramagnetic Curie temperature, and a doping study on the rare-earth site is underway in order to clarify this relationship. However, the general trend shows that both the rare-earth magnetic ordering temperature and the paramagnetic Curie temperature scale with the de Gennes factor.

7 Conclusions

While above T_C =86 K, GdCrSb₃ has very similar magnetic and electrical resistivity properties to those of the light rare-earth chromium antimonides, at lower temperatures very different behavior is found. Both the magnetic susceptibility vs temperature and the magnetization vs field indicate that the system enters a ferrimagnetic phase below 86 K. It is within this ferrimagnetic phase that the anisotropy of the electrical resistivity is clearly evident with insulating behavior found along the stacking axis (the a-axis), and metallic behavior found within the b-c plane. In addition, the de Gennes scaling of itinerant FM and localized rare-earth ordering transition temperatures for RCrSb₃ converge to the 86 K transition of GdCrSb₃. These are all indications of a ferrimagnetic phase in which the itinerant 3d and localized 4f moments are heavily interacting, and anti-aligned.

Acknowledgements

Scott McCall has been very helpful during many discerning discussions. The authors would like to thank Mike Torelli and Donavan Hall for their generous help. We would also like to thank Julia Loewecke for her insightful conversa-

tions. This work was funded by the In House Research Program at the National High Magnetic Field Laboratory, which was funded by the NSF, Cooperative Agreement No. DMR-9527035.

This work was performed under the auspices of the U.S. Department of Energy by the University of California, Lawrence Livermore National Laboratory under Contract W-7405-Eng-48.

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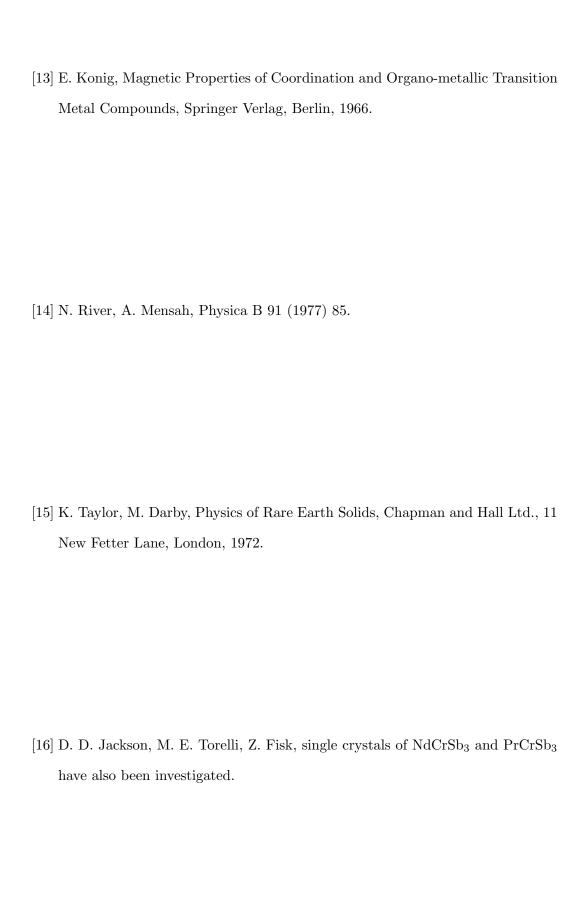


Fig. 1. Field cooled magnetization for the three principle axis of GdCrSb₃. The insets show (a) the RTSb₃ crystal structure, and (b) the high temperature fit to a Curie–Weiss law.

Fig. 2. Magnetization as a function of field for GdCrSb₃ at 5 K. The inset shows the magnetization along the a-axis at 10 K up to 31 T.

Fig. 3. Electrical resistivity of GdCrSb₃ normalized to room temperature. The insets show (a) $d\rho_b/dT$ with a broad peak at the ferrimagnetic Curie temperature, and (b) the $T^{3/2}$ behavior of the resistivity below 86 K.

Fig. 4. a) Inverse magnetic susceptibility along the c-axis for GdVSb₃ with an applied field of 10 kG, with the low temperature susceptibility displayed in the inset showing the AFM transition at 5 K. b) The in-plane electrical resistivity of GdVSb₃ normalized to room temperature.

Fig. 5. The de Gennes scaling for RCrSb $_3$ which show both the Curie temperature due to the Cr ions, and the low temperature ordering due to the rare-earth ions. Both transition temperatures converge at the 86 K transition for R = Gd. Inset shows the paramagnetic Curie temperature, averaged over the three principle axis, which also scales with the de Gennes factor (data from [4,10,16]).

Table 1 Hight temperature Curie-Weiss parameters for $GdTSb_3$ (T=Cr, V). The error in χ_0 is 10%. Sample dimensions of $GdVSb_3$ precluded the measurement along the a-axis.

GdCrSb_3			
axis	$\chi_0 \ (10^{-3} \ \mathrm{emu/mol})$	$\mu_{eff}~(\mu_B/{\rm f.u.})$	θ (K)
a	-1.27	7.89 ± 0.13	-90 ± 12
b	-4.60	10.3 ± 0.3	-88 ± 11
c	-2.45	9.45 ± 0.25	-86 ± 13
GdVSb_3			
b	-0.57	$8.25 \pm .01$	21.5 ± 0.1
<i>c</i>	085	$8.33 \pm .01$	-22.9 ± 0.1

